TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ($L^2-\pi$ -MOSV)

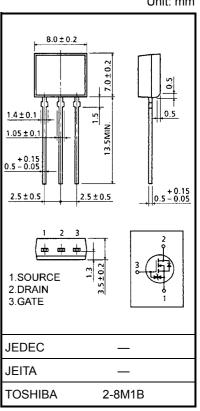
2SK2846

Chopper Regulator, DC-DC Converter and Motor Drive Applications

- Low drain-source ON resistance : RDS (ON) = 4.2 Ω (typ.)
- High forward transfer admittance $: |Y_{fs}| = 1.7 \text{ S} (typ.)$
- Low leakage current : $I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 600 \ V)$
- : $V_{th} = 2.0 \sim 4.0 V (V_{DS} = 10 V, I_D = 1 mA)$ • Enhancement-mode

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	600	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	600	V	
Gate-source voltage	ge	V _{GSS}	±30	V	
Drain current	DC (Note 1)	۱ _D	2	А	
	Pulse (t = 1 ms) (Note 1)			А	
	Pulse (t = 100 µs) (Note 1)	I _{DP}	8	А	
Drain power dissipa	ation	PD	1.3	W	
Single pulse avalanche energy (Note 2)		E _{AS}	93	mJ	
Avalanche current		I _{AR}	2	А	
Repetitive avalanche energy (Note 3)		E _{AR}	0.13	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 0.54 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R _{th (ch−a)}	96.1	°C / W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 41 mH, R_G = 25 Ω , I_{AR} = 2 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm

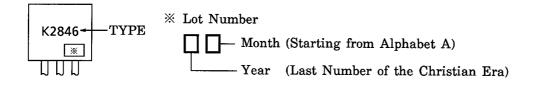
Electrical Characteristics (Ta = 25°C)

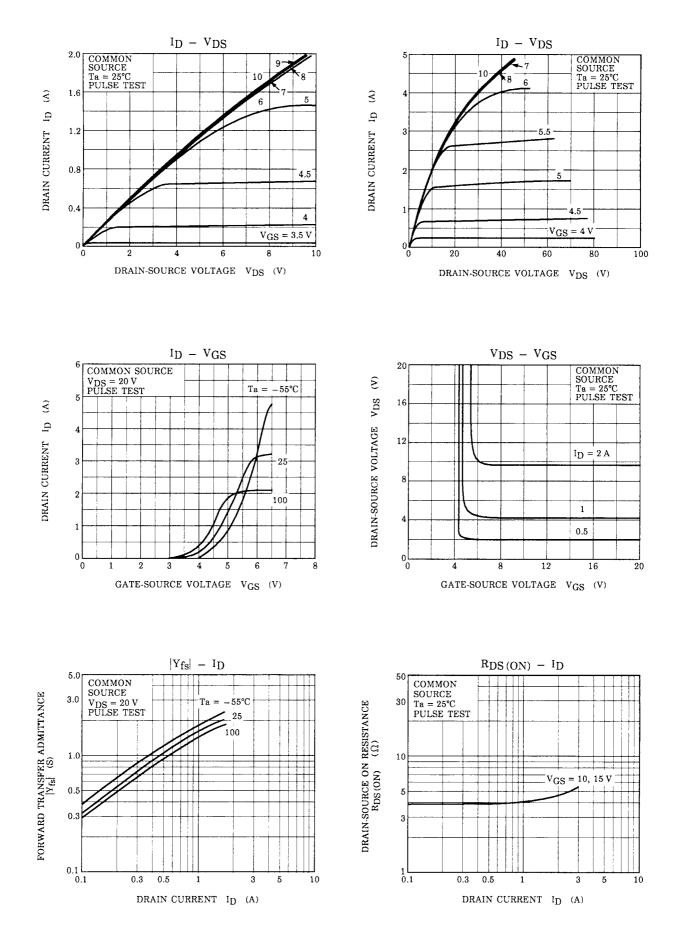
Charae	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V		_	±10	μA
Gate-source br	eakdown voltage	V (BR) GSS	I _D = ±10 μA, V _{GS} = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	μA
Drain-source bi	reakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 1 A	_	4.2	5.0	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 1 A	0.8	1.7	_	S
Input capacitance		C _{iss}		_	380	_	
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	40	_	pF
Output capacitance		C _{oss}			120	_	
Switching time	Rise time	tr	$V_{GS} \stackrel{10V}{}_{0V} \prod_{\substack{OV\\ OV}} \stackrel{I_{D}=1A}{}_{OV} V_{OUT}$	_	15	_	- ns
	Turn-on time	t _{on}		_	25		
	Fall time	t _f		_	20	_	
	Turn-off time	t _{off}	$v_{DD} = 200 v$ Duty $\leq 1\%$, $t_w = 10 \mu s$		80	_	
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ 480 V, V _{GS} = 10 V, I _D = 2 A		9	_	nC
Gate-source charge		Q _{gs}			5	_	
Gate-drain ("miller") Charge		Q _{gd}			4	_	

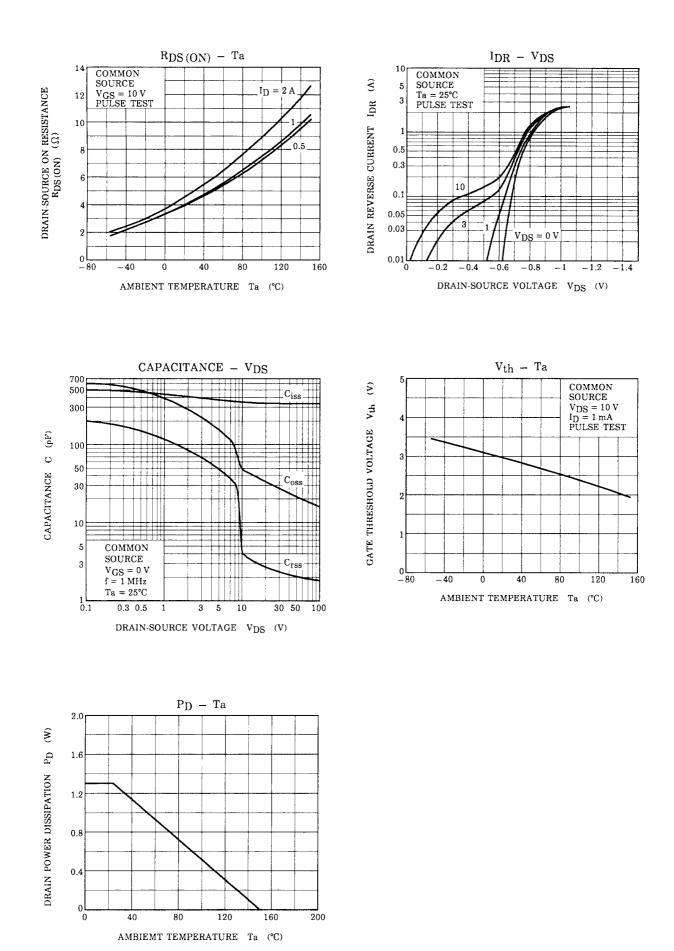
Source–Drain Ratings and Characteristics (Ta = 25°C)

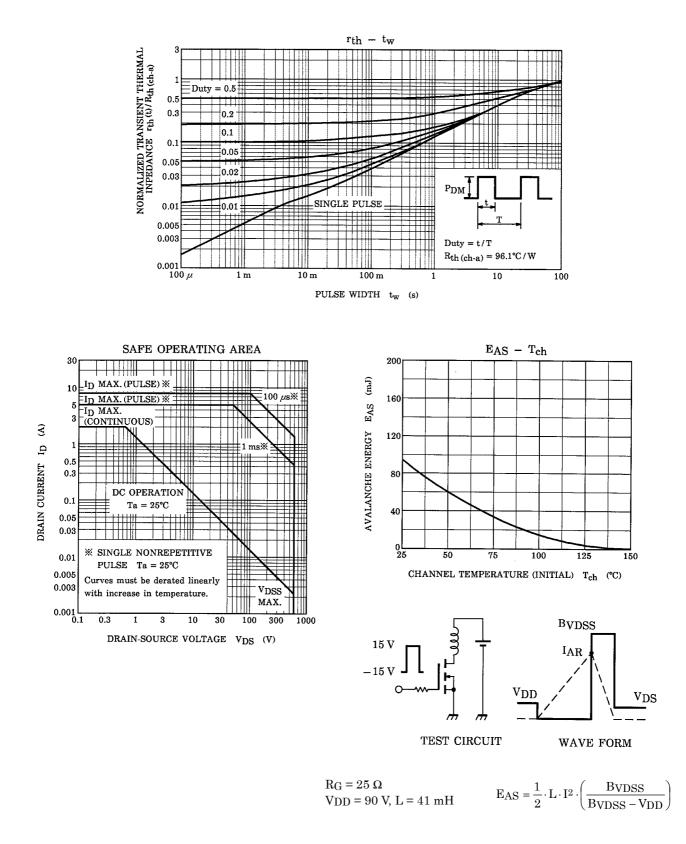
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	2	А
Pulse drain reverse current (Note 1)	I _{DRP}	t = 1 ms	_	_	5	А
	I _{DRP}	t = 100 μs	_	_	8	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 2 A, V _{GS} = 0 V	—	—	-1.5	V
Reverse recovery time	t _{rr}	I _{DR} = 2 A, V _{GS} = 0 V dI _{DR} / dt = 100 A / μs	_	1000	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 100 A / μs		3.5	_	μC

Marking









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